

Application No. 10/642,249

MXIC 1553-3  
(P920080)In the Specification:

Please replace paragraphs [0001] through [0003] of the application with the following amended paragraphs:

[0001] The present application claims the benefit of Provisional U.S. Patent Application No. 60/560,707, entitled PROGRAMMABLE RESISTOR ERASELESS MEMORY, invented by Yeh, et al., and filed on 21 July 2003 (converted application number 10/624,919 from non-provisional status to provisional status).

[0002] The present application is related to U.S. Patent Application No. 10/641,897, entitled METHOD FOR MANUFACTURING A PROGRAMMABLE ERASELESS MEMORY, invented by Yeh, et al., and filed on the same day as the present application. The present application is a continuation-in-part of U.S. Patent Application No. 10/\_\_\_\_\_, entitled PROGRAMMABLE RESISTOR ERASELESS MEMORY, invented by Yeh, et al., and filed on 21 July 2003. Application No. 10/641,897 claims the benefit of Provisional U.S. Patent Application No. 60/560,707, entitled PROGRAMMABLE RESISTOR ERASELESS MEMORY, invented by Yeh, et al., and filed on 21 July 2003 (converted application number 10/624,919 from non-provisional status to provisional status).

[0003] The present application is related to U.S. Patent Application No. 10/641,846, entitled PROGRAMMABLE ERASELESS MEMORY, invented by Yeh, et al., and filed on the same day as the present application. Application No. 10/641,846 claims the benefit of Provisional U.S. Patent Application No. 60/560,707, entitled PROGRAMMABLE RESISTOR ERASELESS MEMORY, invented by Yeh, et al., and filed on 21 July 2003 (converted application number 10/624,919 from non-provisional status to provisional status).